



## Low-Frequency Driver Applications

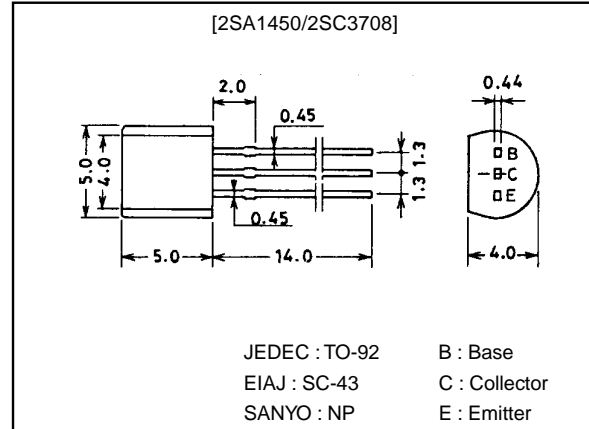
### Features

- Adoption of FBET process.
- AF amp, AF power amp.
- High breakdown voltage :  $V_{CEO} > 80V$

### Package Dimensions

unit:mm

2003A



( ) : 2SA1450

### Specifications

#### Absolute Maximum Ratings at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	$V_{CBO}$		(-)100	V
Collector-to-Emitter Voltage	$V_{CEO}$		(-)80	V
Emitter-to-Base Voltage	$V_{EBO}$		(-)5	V
Collector Current	$I_C$		(-)500	mA
Collector Current (Pulse)	$I_{CP}$		(-)800	mA
Base Current	$I_B$		(-)100	mA
Collector Dissipation	$P_C$		600	mW
Junction Temperature	$T_j$		150	$^\circ C$
Storage Temperature	$T_{stg}$		-55 to +150	$^\circ C$

#### Electrical Characteristics at $T_a = 25^\circ C$

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = (-)60V, I_E = 0$			(-)0.1	$\mu A$
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	$\mu A$
DC Current Gain	$h_{FE1}$	$V_{CE} = (-)5V, I_C = (-)50mA$	100*		400*	
	$h_{FE2}$	$V_{CE} = (-)5V, I_C = (-)400mA$	60			
Gain-Bandwidth Product	$f_T$	$V_{CE} = (-)10V, I_C = (-)10mA$		120		MHz
Output Capacitance	$C_{ob}$	$V_{CB} = (-)10V, f = 1MHz$		(7)5		pF
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)400mA, I_B = (-)40mA$		0.16		V
				(-0.2)	(-0.5)	V
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)400mA, I_B = (-)40mA$		(-)0.9	(-)1.2	V
Collector-to-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	-100			V
Collector-to-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	-80			V
Emitter-to-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	-5			V

\* : 2SA1450/2SC3708 are classified by 50mA  $h_{FE}$  as follows :

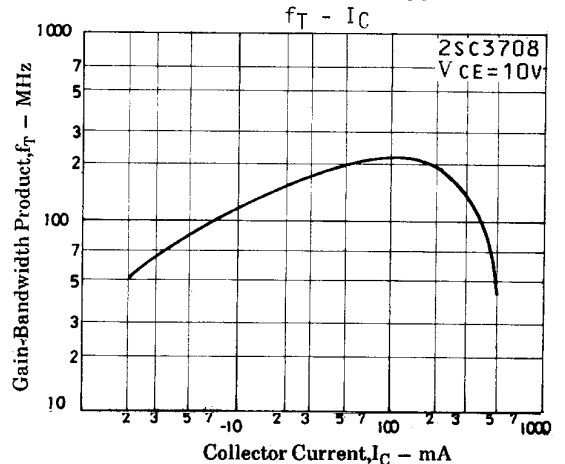
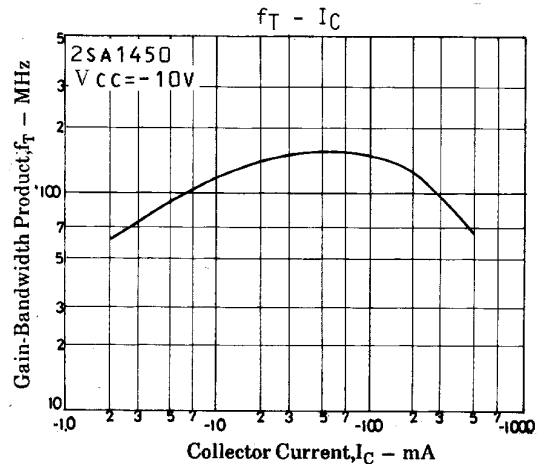
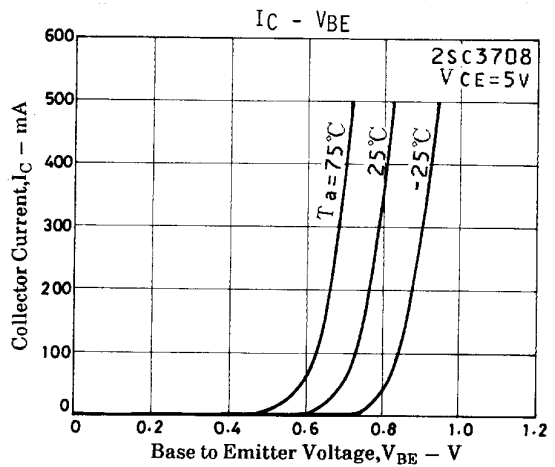
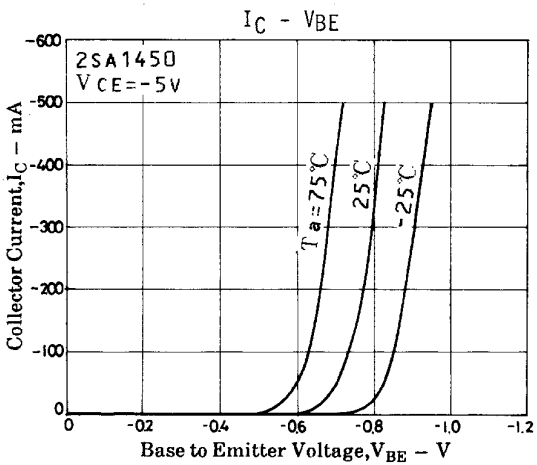
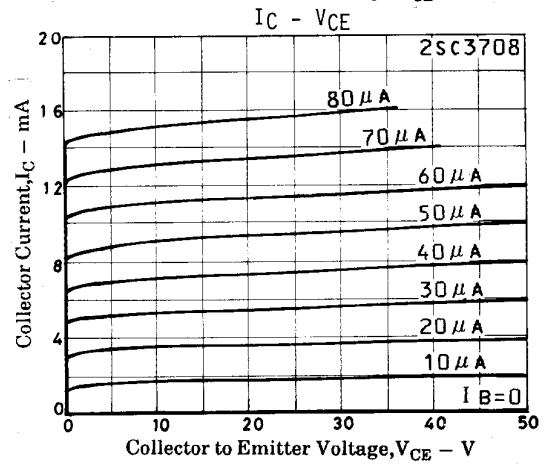
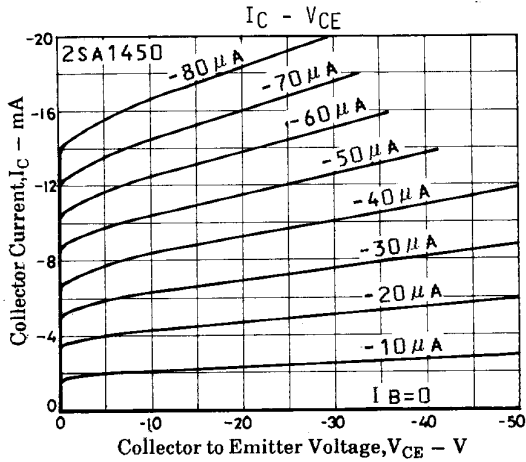
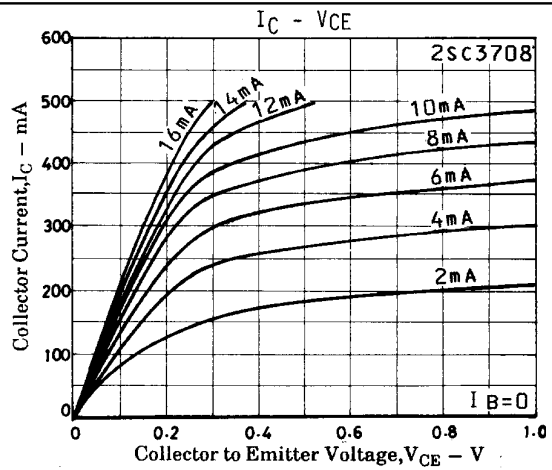
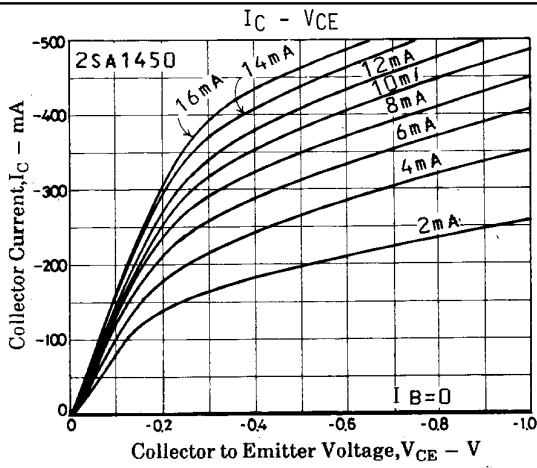
100	R	200	140	S	280	200	T	400
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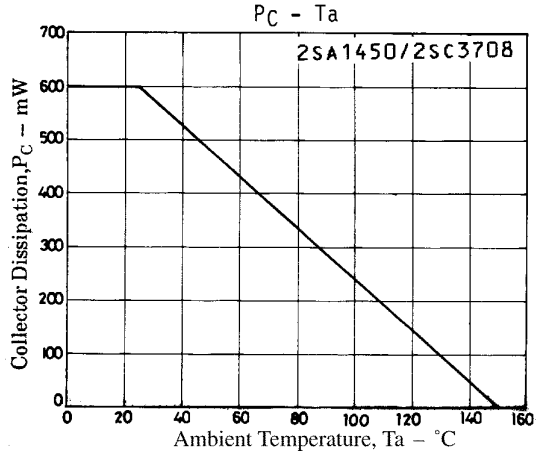
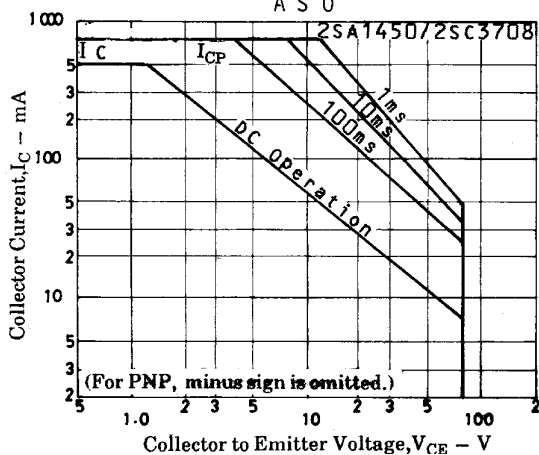
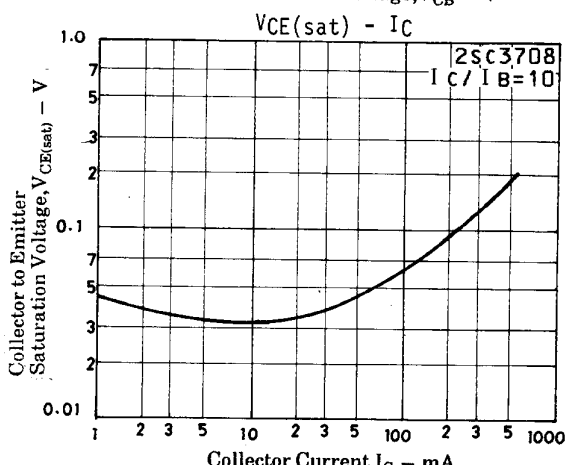
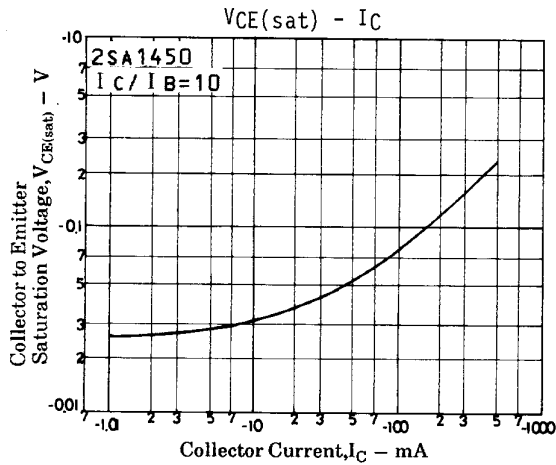
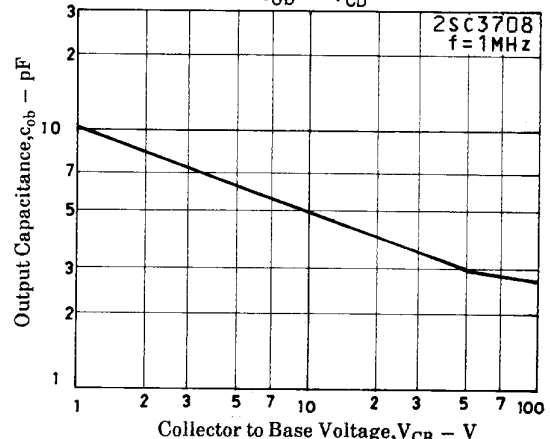
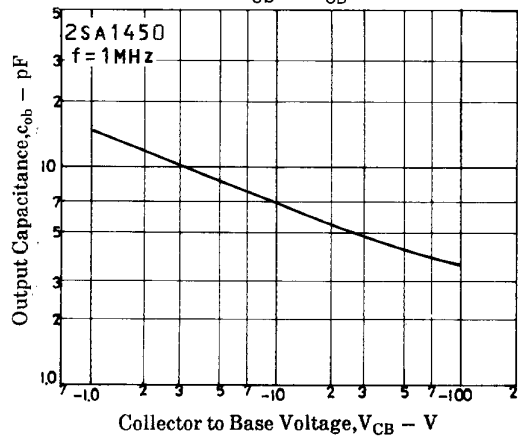
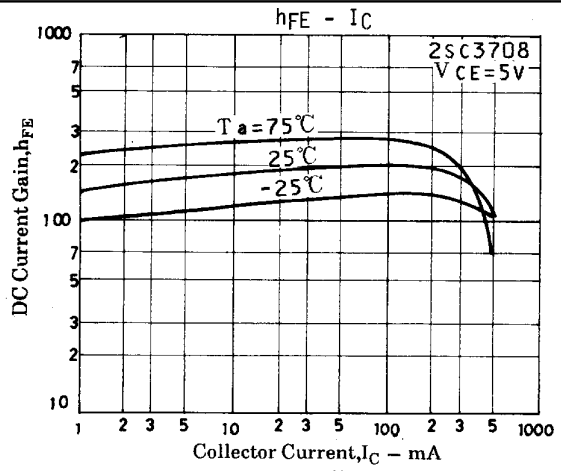
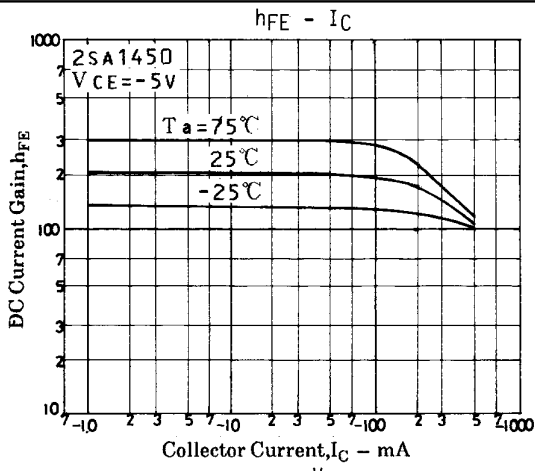
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# 2SA1450/2SC3708



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